



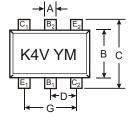
NPN DUAL SMALL SIGNAL SURFACE MOUNT TRANSISTOR

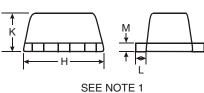
Features

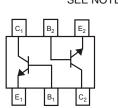
- Epitaxial Die Construction
- Complementary PNP Type Available (BC857BV)
- Ultra-Small Surface Mount Package
- Lead Free By Design/RoHS Compliant (Note 3)

Mechanical Data

- Case: SOT-563
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture sensitivity: Level 1 per J-STD-020C
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Marking (See Page 2): K4V
- Ordering & Date Code Information: See Page 2
- Weight: 0.002 grams (approx.)







SOT-563								
Dim	Min Max Typ							
Α	0.15	0.30	0.25					
В	1.10 1.25 1.20							
С	1.55 1.70 1.60							
D	0.50							
G	0.90 1.10 1.00							
Н	1.50 1.70 1.60							
K	0.56 0.60 0.60							
L	0.10 0.30 0.20							
М	0.10 0.18 0.11							
All Dimensions in mm								

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Maximum Ratings @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit		
Collector-Base Voltage	V _{CBO}	50	V		
Collector-Emitter Voltage	V _{CEO}	45	V		
Emitter-Base Voltage	V _{EBO}	6.0	V		
Collector Current	Ic	100	mA		
Power Dissipation (Note 2)	Pd	150	mW		
Thermal Resistance, Junction to Ambient (Note 2)	$R_{ heta JA}$	833	°C/W		
Operating and Storage Temperature Range	T _j , T _{STG}	-55 to +150	°C		

Notes:

- 1. Package is non-polarized. Parts may be on reel in orientation illustrated, 180° rotated, or mixed (both ways).
- 2. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- 3. No purposefully added lead.



Electrical Characteristics @ T_A = 25°C unless otherwise specified

Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage (Note 4)		V _{(BR)CBO}	50	_	_	V	$I_C = 10 \mu A, I_B = 0$
Collector-Emitter Breakdown Voltage	(Note 4)	V _{(BR)CEO}	45	_	_	٧	$I_C = 10 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	(Note 4)	V _{(BR)EBO}	6	_	_	V	$I_E = 1 \mu A, I_C = 0$
DC Current Gain (Note 4)		h _{FE}	200	290	450	_	V _{CE} = 5.0V, I _C = 2.0mA
Collector-Emitter Saturation Voltage (Note 4)		V _{CE(SAT)}	_	_	100 300	mV	I _C = 10mA, I _B = 0.5mA I _C = 100mA, I _B = 5.0mA
Base-Emitter Saturation Voltage (Note 4)		V _{BE(SAT)}	_	700 900	_	mV	$I_C = 10$ mA, $I_B = 0.5$ mA $I_C = 100$ mA, $I_B = 5.0$ mA
Base-Emitter Voltage (Note 4)		V _{BE}	580 —	660 —	700 770	mV	V _{CE} = 5.0V, I _C = 2.0mA V _{CE} = 5.0V, I _C = 10mA
Collector-Emitter Cutoff Current (Note 4)		I _{CBO}	_	_	15 5.0	nΑ μΑ	V _{CB} = 30V V _{CB} = 30V, T _A = 150°C
Gain Bandwidth Product		f⊤	100	_	_	MHz	V _{CE} = 5.0V, I _C = 10mA, f = 100MHz
Output Capacitance		C _{OBO}	_	_	4.5	pF	V _{CB} = 10V, f = 1.0MHz
Noise Figure		NF	_	_	10	dB	$V_{CE} = 5V, R_S = 2.0k\Omega,$ f = 1.0kHz, BW = 200Hz

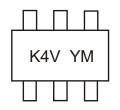
Ordering Information (Note 5)

Device	Packaging	Shipping			
BC847BV-7	SOT-563	3000/Tape & Reel			

Notes:

- 4. Short duration pulse test used to minimize self-heating effect.
- 5. For Packaging Details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



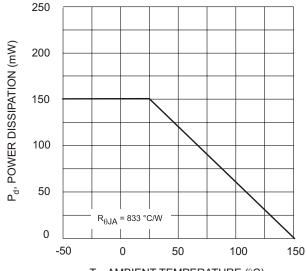
K4V = Product Type Marking Code YM = Date Code Marking Y = Year (ex: P = 2003) M = Month (ex: 9 = September)

Date Code Key

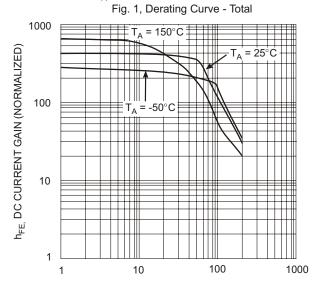
Year	2003	2004	2005	2006	2007	2008	2009	
Code	Р	R	S	Т	U	V	W	

Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

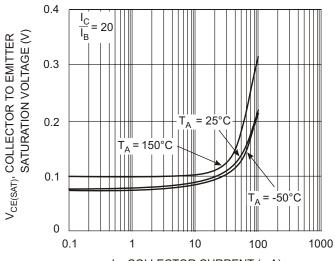




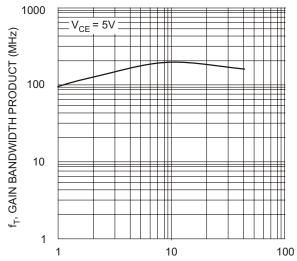
T_A, AMBIENT TEMPERATURE (°C)



 $\rm I_{C}$, COLLECTOR CURRENT (mA) Fig. 3, DC Current Gain vs Collector Current



I_C, COLLECTOR CURRENT (mA)
Fig. 2, Collector Emitter Saturation Voltage
vs. Collector Current



I_C, COLLECTOR CURRENT (mA)
Fig. 4, Gain Bandwidth Product vs Collector Current